## $\begin{array}{c} \text{Homework} \ \#7 \\ \text{Computational Microelectronics} \end{array}$

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## 1 Results

We have calculated the electron density and integrated electron density by solving the Schrödinger equation of 3D infinite potential well. Note that, by setting  $L_x = L_y = 100$  nm and  $L_z = 0.5$  nm, we approximately the quantum number about z-direction  $n_z$  as a subband number. We find that the integrated electron density increases with the Fermi energy  $E_F$ . And the electron density also increases and become more flat near the midpoint in the z-direction.

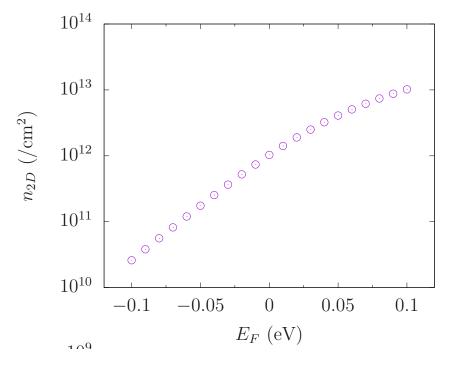


Figure 1: The integrated electron density  $n_{2D}$  as a function of the Fermi energy  $E_F$ .

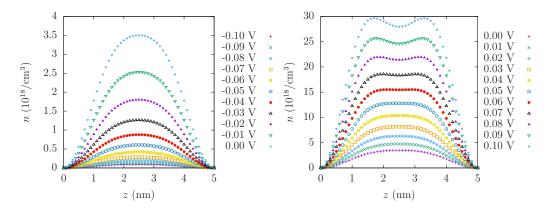


Figure 2: Snapshot of the electron density  $n_{3D}$  in the z-direction.